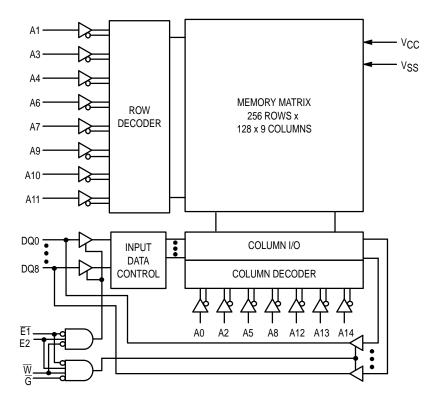
32K x 9 Bit Fast Static RAM

The MCM6205D is fabricated using Motorola's high–performance silicon–gate CMOS technology. Static design eliminates the need for external clocks or timing strobes, while CMOS circuitry reduces power consumption and provides for greater reliability.

This device meets JEDEC standards for functionality and pinout, and is available in a plastic small—outline J—leaded package.

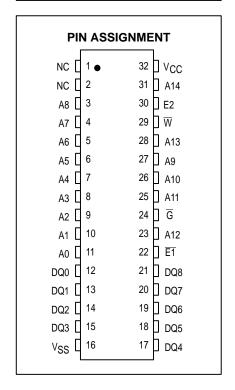
- Single 5 V ± 10% Power Supply
- Fully Static No Clock or Timing Strobes Necessary
- Fast Access Times: 15, 20, and 25 ns
- Equal Address and Chip Enable Access Times
- Output Enable (G) Feature for Increased System Flexibility and to Eliminate Bus Contention Problems
- Low Power Operation: 130 140 mA Maximum AC
- Fully TTL Compatible Three State Output

BLOCK DIAGRAM



MCM6205D





A0 – A14 Address Input DQ0 – DQ8 Data Input/Data Output
W Write Enable G Output Enable E1, E2 Chip Enable NC No Connection VCC Power Supply (+ 5 V) VSS Ground

REV 1 5/95



TRUTH TABLE (X = Don't Care)

E1	E2	G	W	Mode	V _{CC} Current	Output	Cycle
Н	Х	Х	Χ	Not Selected	I _{SB1} , I _{SB2}	High–Z	_
Χ	L	Х	Х	Not Selected	ISB1, ISB2	High–Z	_
L	Н	Н	Н	Output Disabled	ICCA	High–Z	_
L	Н	L	Н	Read	ICCA	D _{out}	Read Cycle
L	Н	Х	L	Write	ICCA	High–Z	Write Cycle

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage	Vcc	- 0.5 to + 7.0	V
Voltage Relative to VSS For Any Pin Except VCC	V _{in} , V _{out}	- 0.5 to V _{CC} + 0.5	V
Output Current	l _{out}	± 20	mA
Power Dissipation	PD	1.0	W
Temperature Under Bias	T _{bias}	- 10 to + 85	°C
Operating Temperature	T _A	0 to + 70	°C
Storage Temperature — Plastic	T _{stg}	- 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high–impedance circuit.

This CMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 5.0 \text{ V} \pm 10\%, T_A = 0 \text{ to } 70^{\circ}\text{C}, \text{Unless Otherwise Noted})$

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc	4.5	5.0	5.5	V
Input High Voltage	VIH	2.2	_	V _{CC} + 0.3**	V
Input Low Voltage	VIL	- 0.5*	_	0.8	V

^{*} V_{IL} (min) = -0.5 V dc; V_{IL} (min) = -2.0 V ac (pulse width ≤ 20 ns)

DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V _{in} = 0 to V _{CC})	llkg(I)	_	± 1	μΑ
Output Leakage Current ($\overline{E1} = V_{IH}$ or $\overline{G} = V_{IH}$ or $E2 = V_{IL}$, $V_{out} = 0$ to V_{CC})	l _{lkg(O)}	_	± 1	μА
Output High Voltage (I _{OH} = – 4.0 mA)	Vон	2.4	_	V
Output Low Voltage (I _{OL} = 8.0 mA)	VOL	_	0.4	٧

POWER SUPPLY CURRENTS

Parameter	Symbol	– 15	- 20	- 25	Unit
AC Active Supply Current ($I_{Out} = 0 \text{ mA}, V_{CC} = Max, f = f_{max}$)	ICCA	140	135	130	mA
AC Standby Current ($\overline{E1} = V_{IH}$, or $E2 = V_{IL}$, $V_{CC} = Max$, $f = f_{max}$)	I _{SB1}	40	40	35	mA
CMOS Standby Current (V _{CC} = Max, f = 0 MHz, $\overline{E1} \ge$ V _{CC} $-$ 0.2 V or E2 \le V _{SS} + 0.2 V, V _{in} \le V _{SS} + 0.2 V, or \ge V _{CC} $-$ 0.2 V)	I _{SB2}	20	20	20	mA

MCM6205D MOTOROLA FAST SRAM

^{**} V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width \leq 20 ns)

CAPACITANCE (f = 1 MHz, dV = 3 V, T_A = 25°C, Periodically sampled rather than 100% tested)

Characteristic	Symbol	Max	Unit
Address Input Capacitance	C _{in}	6	pF
Control Pin Input Capacitance (E1, E2, G, W)	C _{in}	8	pF
I/O Capacitance	C _{I/O}	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(VCC = 5.0 V \pm 10%, TA = 0 to + 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level 1.5 V	Output Timing Measurement Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V	Output Load Figure 1A Unless Otherwise Noted
Input Rise/Fall Time 5 ns	

READ CYCLE (See Notes 1 and 2)

		MCM6205D-15		MCM6205D-20		MCM6205D-25			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	t _{AVAV}	15	_	20	_	25	_	ns	3
Address Access Time	^t AVQV	_	15	_	20	_	25	ns	
Enable Access Time	^t ELQV	_	15	_	20	_	25	ns	4
Output Enable Access Time	^t GLQV	_	8	_	10	_	12	ns	
Output Hold from Address Change	^t AXQX	4	_	4	_	4	_	ns	
Enable Low to Output Active	^t ELQX	4	_	4	_	4	_	ns	5, 6, 7
Enable High to Output High-Z	^t EHQZ	0	8	0	9	0	10	ns	5, 6, 7
Output Enable Low to Output Active	^t GLQX	0	_	0	_	0	_	ns	5, 6, 7
Output Enable High to Output High–Z	^t GHQZ	0	7	0	8	0	10	ns	5, 6, 7
Power Up Time	tELICCH	0	_	0	_	0	_	ns	
Power Down Time	^t EHICCL	_	15	_	20	_	25	ns	

NOTES:

- 1. W is high for read cycle.
- 2. $\overline{E1}$ and E2 are represented by \overline{E} in this data sheet. E2 is of opposite polarity to \overline{E} .
- 3. All timings are referenced from the last valid address to the first transitioning address.
- 4. Addresses valid prior to or coincident with \overline{E} going low.
- 5. At any given voltage and temperature, t_{EHQZ} (max) is less than t_{ELQX} (min), and t_{GHQZ} (max) is less than t_{GLQX} (min), both for a given device and from device to device.
- 6. Transition is measured $\pm\,500$ mV from steady–state voltage with load of Figure 1B.
- 7. This parameter is sampled and not 100% tested.
- 8. Device is continuously selected ($\overline{E1} = V_{IL}$, $E2 = V_{IH}$, $\overline{G} = V_{IL}$).

AC TEST LOADS

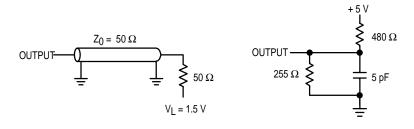


Figure 1A

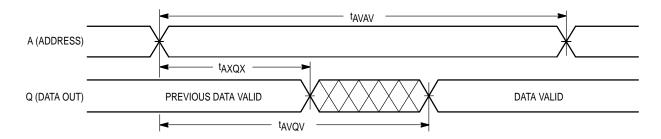
Figure 1B

TIMING LIMITS

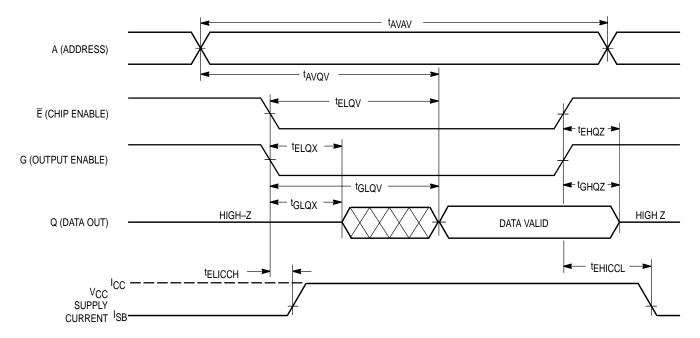
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

MOTOROLA FAST SRAM MCM6205D

READ CYCLE 1 (See Note 8)



READ CYCLE 2 (See Note 4)



MCM6205D MOTOROLA FAST SRAM

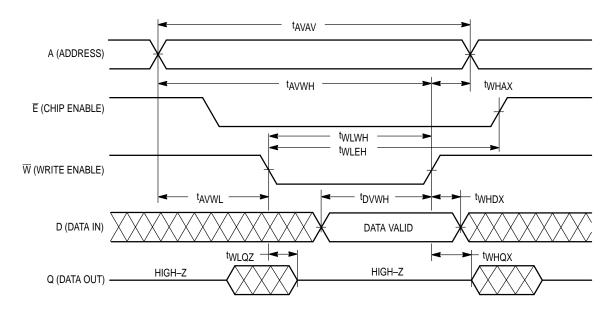
WRITE CYCLE 1 (W Controlled, See Notes 1, 2, and 3)

		MCM6205D-15		MCM6205D-20		MCM6205D-25			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Units	Notes
Write Cycle Time	t _{AVAV}	15	_	20	_	25	_	ns	4
Address Setup Time	t _{AVWL}	0	_	0	_	0	_	ns	
Address Valid to End of Write	^t AVWH	12	_	15	_	20	_	ns	
Write Pulse Width	tWLWH, tWLEH	12	_	15	_	20	_	ns	
Write Pulse Width, G High	tWLWH, tWLEH	10	_	12	_	15	_	ns	5
Data Valid to End of Write	tDVWH	7	_	8	_	10	_	ns	
Data Hold Time	tWHDX	0	_	0	_	0	_	ns	
Write Low to Output High–Z	tWLQZ	0	7	0	8	0	10	ns	6, 7, 8
Write High to Output Active	tWHQX	4	_	4	_	4	_	ns	6, 7, 8
Write Recovery Time	tWHAX	0	_	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of \overline{E} low and \overline{W} low.
- 2. $\overline{E1}$ and E2 are represented by \overline{E} in this data sheet. E2 is of opposite polarity to \overline{E} .
- 3. If \overline{G} goes low coincident with or after \overline{W} goes low, the output will remain in a high impedance state.
- 4. All timings are referenced from the last valid address to the first transitioning address.
- 5. If $\overline{G} \ge V_{IH}$, the output will remain in a high impedance state.
- 6. At any given voltage and temperature, t_{WLQZ} (max) is less than t_{WHQX} (min), both for a given device and from device to device.
 7. Transition is measured ± 500 mV from steady–state voltage with load of Figure 1B.
- 8. This parameter is sampled and not 100% tested.

WRITE CYCLE 1 (W Controlled, See Notes 1, 2, and 3)



MOTOROLA FAST SRAM MCM6205D

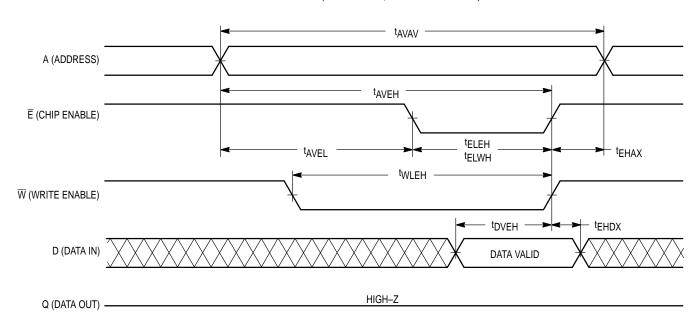
WRITE CYCLE 2 (E Controlled, See Notes 1 and 2)

		MCM6205D-15		MCM6205D-20		0 MCM6205D-25			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	t _{AVAV}	15	_	20	_	25	_	ns	3
Address Setup Time	^t AVEL	0	_	0	_	0	-	ns	
Address Valid to End of Write	^t AVEH	12	_	15	_	20	_	ns	
Enable to End of Write	tELEH, tELWH	10	_	12	_	15	_	ns	4, 5
Data Valid to End of Write	^t DVEH	7	_	8	_	10	-	ns	
Data Hold Time	^t EHDX	0	_	0	_	0		ns	
Write Recovery Time	^t EHAX	0	_	0	_	0	_	ns	

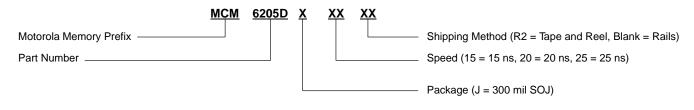
NOTES:

- 1. A write occurs during the overlap of \overline{E} low and \overline{W} low.
- 2. $\overline{E1}$ and E2 are represented by \overline{E} in this data sheet. E2 is of opposite polarity to \overline{E} .
- 3. All timings are referenced from the last valid address to the first transitioning address.
- 4. If \overline{E} goes low coincident with or after \overline{W} goes low, the output will remain in a high impedance state.
- 5. If E goes high coincident with or before W goes high, the output will remain in a high impedance state.

WRITE CYCLE 2 (E Controlled, See Notes 1 and 2)



ORDERING INFORMATION (Order by Full Part Number)



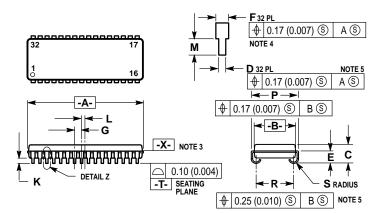
Full Part Numbers — MCM6205DJ15 MCM6205DJ15R2 MCM6205DJ20 MCM6205DJ20R2

MCM6205DJ25 MCM6205DJ25R2

MCM6205D MOTOROLA FAST SRAM

PACKAGE DIMENSIONS

CASE 857-02 32 LEAD 300 MIL SOJ



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DATUM PLANE -X- LOCATED AT TOP OF MOLD PARTING LINE AND COINCIDENT WITH TOP OF LEAD, WHERE LEAD EXITS BODY.
- TO BE DETERMINED AT PLANE -X-. TO BE DETERMINED AT PLANE -T-.
- DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION. MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 7. 857-01 IS OBSOLETE, NEW STANDARD 857-02.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	20.83	21.08	0.820	0.830
В	7.50	7.74	0.295	0.305
С	3.26	3.75	0.128	0.148
D	0.41	0.50	0.016	0.020
E	2.24	2.48	0.088	0.098
F	0.67	0.81	0.026	0.032
G	1.27	BSC	0.050	BSC
K	0.89	1.14	0.035	0.045
L	0.64	BSC	0.02	BSC
N	0.76	1.14	0.030	0.045
Р	8.38	8.64	0.330	0.340
R	6.60	6.86	0.260	0.270
S	0.77	1.01	0.030	0.040

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and una registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

MOTOROLA FAST SRAM MCM6205D

Literature Distribution Centers:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036.

JAPAN: Nippon Motorola Ltd.; 4-32–1, Nishi–Gotanda, Shinagawa–ku, Tokyo 141, Japan.

ASIA PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Center, No. 2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong.



